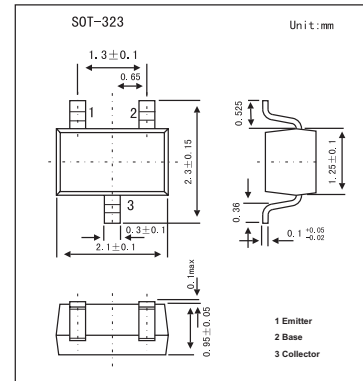


Silicon PNP Epitaxial Planar Type

2SB1218

■ Features

- High forward current transfer ratio h_{FE} .

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-45	V
Collector-emitter voltage	V_{CEO}	-45	V
Emitter-base voltage	V_{EBO}	-7	V
Peak collector current	I_{CP}	-200	A
Collector current	I_C	-100	A
Collector power dissipation	P_C	150	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base voltage	V_{CBO}	$I_C = -10 \mu\text{A}, I_E = 0$	-45			V
Collector-emitter voltage	V_{CEO}	$I_C = -2 \text{ mA}, I_B = 0$	-45			V
Emitter-base voltage	V_{EBO}	$I_E = -10 \mu\text{A}, I_C = 0$	-7			V
Collector-base cutoff current	I_{CBO}	$V_{CB} = -20 \text{ V}, I_E = 0$			-0.1	μA
Collector-emitter cutoff current	I_{CEO}	$V_{CE} = -10 \text{ V}, I_B = 0$			-100	μA
Forward current transfer ratio	h_{FE}	$V_{CE} = -10 \text{ V}, I_C = -2 \text{ mA}$	160		460	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -100 \text{ mA}, I_B = -10 \text{ mA}$		-0.3	-0.5	V
Transition frequency	f_T	$V_{CB} = -10 \text{ V}, I_E = 1 \text{ mA}, f = 200 \text{ MHz}$		80		MHz
Collector output capacitance	C_{ob}	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		2.7		pF

■ h_{FE} Classification

Marking	BQ	BR	BS	B
Rank	Q	R	S	No-rank
h_{FE}	160~260	210~340	290~460	160~460